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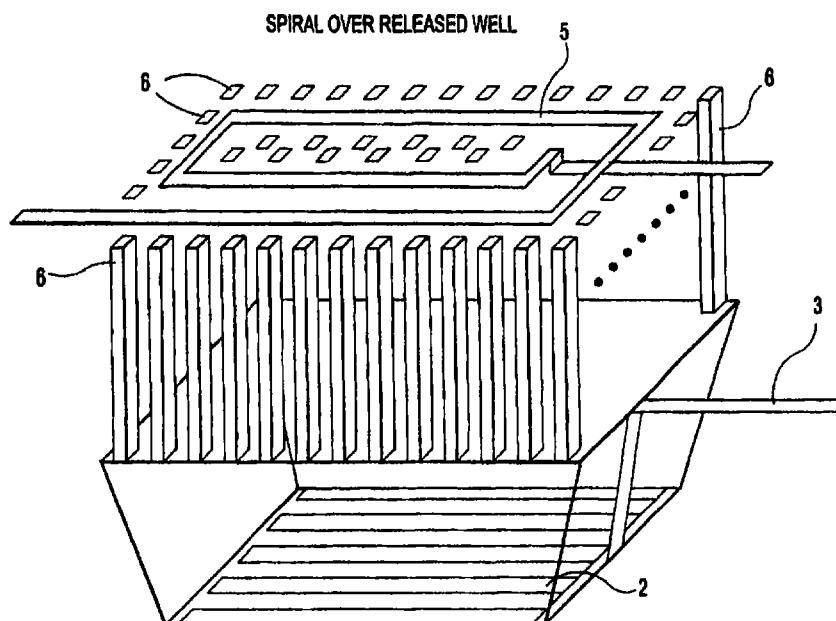
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(54) Title: HIGH Q INDUCTOR WITH FARADAY SHIELD AND DIELECTRIC WELL BURIED IN SUBSTRATE



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(57) Abstract: Inductor losses to a semiconducting substrate are eliminated in an IC structure by etching a well into the substrate down to the insulating layer coating the substrate and fabricating a grounded Faraday shield in the shape of elongated segments in the bottom of the well. The well lies directly below the inductor and is optionally filled with cured low-k organic dielectric or air.

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